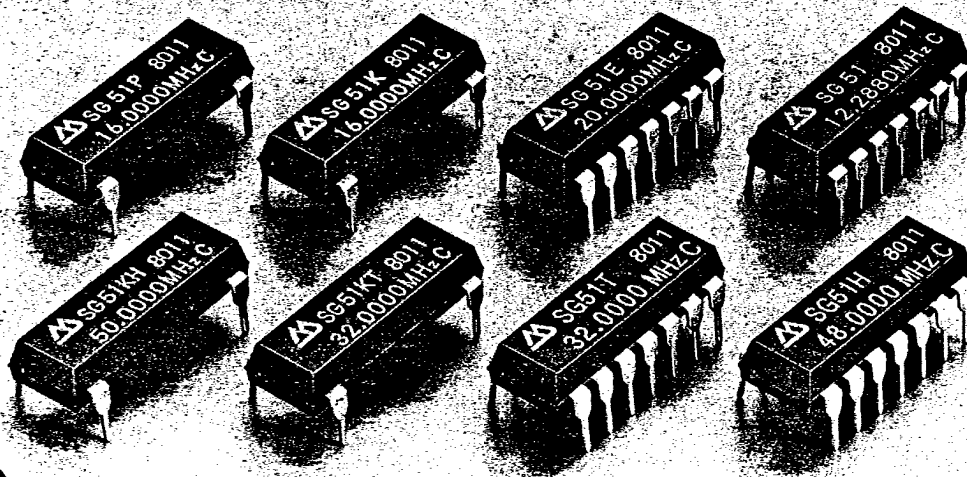


CMOS CRYSTAL OSCILLATOR SG-51 Series



- SG-51 ● SG-51T
- SG-51K ● SG-51H
- SG-51E ● SG-51KT
- SG-51P ● SG-51KH

- High reliability by cylinder type AT Crystal
 - Automatic mountable
- Lower current consumption by C-MOS IC
 - TTL-10 output load by using C-MOS IC
 - DIP 14 PIN plastic package
- Output enable with standby function
- DIP4PIN plastic package compatible with metal package oscillator (SG-31 series)

EPSON AMERICA, INC.

■ SPECIFICATION (CHARACTERISTICS)

Item		Symbol	SG-51/51K/51E/51P	
			Specification	Remarks
Output Frequency Range		F ₀	1.5000MHz~25.0000MHz	
Input Voltage	Operating Voltage	V _{DD}	5.0±0.5V	
	Maximum Supply Voltage	V _{DD} -V _{SS}	-0.3~+7.0V	
Temperature Range	Operating Temperature	T _{OPR}	-10~+70°C	
	Storage Temperature	T _{STG}	-55~+125°C	
Soldering Condition	Lead	T _{SOL}	Temperature 260°C MAX. For 10sec MAX.	Molding part 150°C MAX.
Frequency Stability		ΔF ₀	C: ±100ppm	
Aging		f _{ag}	±20ppm/year Max. ±3ppm/year TYP.	25°C V _{DD} =5.0V The first year
Input Current		I _{OP}	10mA(12MHz) TYP. 23mA MAX.	Without load
Duty		T _w /T	4Q~60%	1.4V or 1/2 V _{DD} level
Output Voltage		V _{OH}	V _{DD} -0.4V MIN.	I _{OH} =-400mA
		V _{OL}	0.4V MAX.	I _{OL} =16mA
Input Voltage (SG-51E,51P)		V _{IH}	2.0V MIN.	I _{IH} =1μA (V _{IH} =V _{DD})
		V _{IL}	0.8V MAX.	I _{IL} =-100μA (V _{IL} =GND)
Output Rise Time		t _{TLH}	8 nsec MAX. 5 nsec TYP.	C-MOS Load: 20% V _{DD} ↔80%V _{DD} TTL Load: 0.4V↔2.4V Refer to the timing chart
Output Fall Time		t _{THL}	8 nsec MAX. 5 nsec TYP.	
Oscillation Time		t _{osc}	10 msec MAX. 0.3 msec TYP.(12MHz MIN.)	t of rise time 4.5V should be 0 more than 150μsec. at V _{DD} =0~4.5V

NOTES: Characteristics is standard by above-mentioned operating temperature and input voltage without any notes.

■ FREQUENCY LIST

Model \ Frequency	2.5MHz	25MHz	30MHz	36MHz	54.999MHz
SG-51,51K,51E,51P					
SG-51T,SG-51KT					
SG-51H,SG-51KH					

■ OUTPUT FREQUENCIES(TYPICAL)

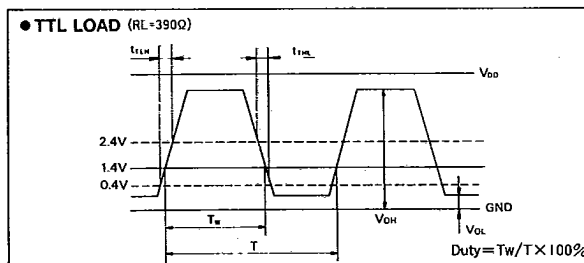
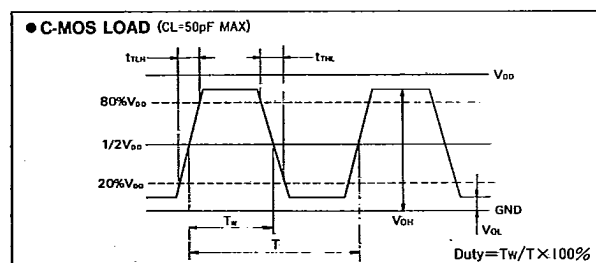
Model	Output Frequencies	
SG-51 51K 51E 51P	2.4576MHz	3.0720MHz
	4.0000MHz	4.9152MHz
	6.0000MHz	6.1440MHz
	8.0000MHz	9.2160MHz
	9.8304MHz	10.0000MHz
	12.0000MHz	12.2880MHz
	16.0000MHz	18.4320MHz
	19.6608MHz	20.0000MHz
	24.0000MHz	
SG-51T 51KT	30.0000MHz	32.0000MHz
	33.3333MHz	36.0000MHz
SG-51H 51KH	30.0000MHz	32.0000MHz
	33.3333MHz	36.0000MHz
	40.0000MHz	48.0000MHz
	50.0000MHz	

■ FUNCTION LIST

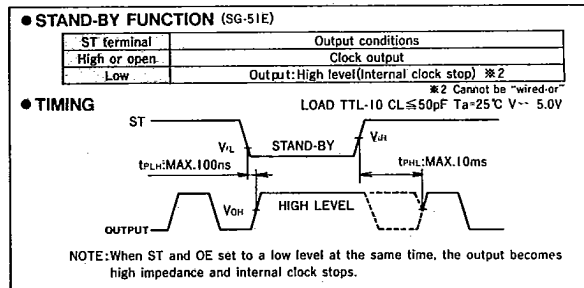
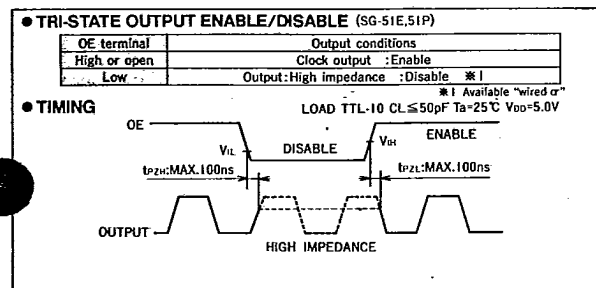
Model	Terminal		Load Condition		Output Control Function	
	DIP14PIN	DIP 4PIN	C-MOS	TTL-10	OE Function	ST Function
SG-51	○		○	○		
SG-51K		○	○	○		
SG-51E	○		○	○	○	○
SG-51P		○	○	○	○	
SG-51T	○			○		
SG-51H	○		○			
SG-51KT		○		○		
SG-51KH		○	○			

SG-51T/51KT		SG-51H/51KH	
Specification	Remarks	Specification	Remarks
25.0000MHz~36.0000MHz		30.0000MHz~54.9999MHz	
5.0±0.5V		5.0±0.5V	
-0.3~+7.0V		-0.3~+7.0°C	
-10~+70°C		-10~+70°C	
-55~+100°C		-55~+100°C	
Temperature 260°C MAX. For 10sec MAX.	Molding part 150°C MAX.	Temperature 260°C MAX. For 10sec MAX.	Molding part 150°C MAX.
C: ±100ppm		C: ±100ppm	
±20ppm/year MAX. ±3ppm/year TYP.	25°C, V _{DD} =5.0V The first year	±20ppm/year MAX. ±3ppm/year TYP.	25°C, V _{DD} =5.0V The first year
35mA MAX. 25mA(32MHz)TYP.	Without load	32mA MAX. 20mA(54MHz)TYP.	Without load
40~60%	1.4V level	40~60%	1/2 V _{DD} level
V _{DD} -0.4V MIN.	I _{OH} = -400μA	V _{DD} -0.37V MIN.	I _{OH} = -4mA
0.4V MAX.	I _{OL} =16mA	0.37V MAX.	I _{OL} =4mA
10nsec MAX. 5nsec TYP.	TTL load: 0.4V↔2.4V Refer to the timing chart	7nsec MAX. 3.5nsec TYP.	C-MOS load: 20%V _{DD} ↔80%V _{DD} Refer to the timing chart
8nsec MAX. 3nsec TYP.		7nsec MAX. 3.5nsec. TYP.	
10msec. MAX. 5msec TYP.	t of rise time 4.5V should be 0 more than 1msec. at V _{DD} =0~4.5V	10msec. MAX. 3msec TYP.	t of rise time 4.5V should be 0 more than 1msec. at V _{DD} =0~4.5V

OUTPUT WAVEFORM



OUTPUT ENABLE & STAND-BY



RELIABILITY TEST

2H-24HS later than test

Test Items	Conditions	Standard	Conform to test way
Continuous operating	70°C × 5V × 1000H	±20ppm *1	JIS C-7022 B-1
High Temperature and Humidity bias	85°C × 85% × 5V × 1000H	±20ppm *1, *2	JIS C-7022 B-5
Temperature Cycle	-55°C ↔ 125°C × no input voltage 100 cycle, Leave it 30 min, by each temperature	*1	JIS C-7022 A-4
Steam Pressurization (P. C. T.)	121°C × 2 atoms (96%) × 5V × 96H	*1	EIAJ-SD-121 18
Oscillation	10-500Hz 15mmp-p or 10G 10Hz → 500Hz → 10Hz 15min./cycle Logarithm 6H (3 direction 2H each)	±10ppm *1	JIS C-7022 A-10
Shock Resistance	Dropping 3 times from a height of 750mm on to a hard wooden plate. (Approx. 5000G)	±20ppm *1	JIS C-7022 A-8
Solder heat resistance	To dipping it for 10 second above 1mm from the lead terminal in the solder bath with 260°C ± 10°C	±10ppm *1	JIS C-7022 A-1

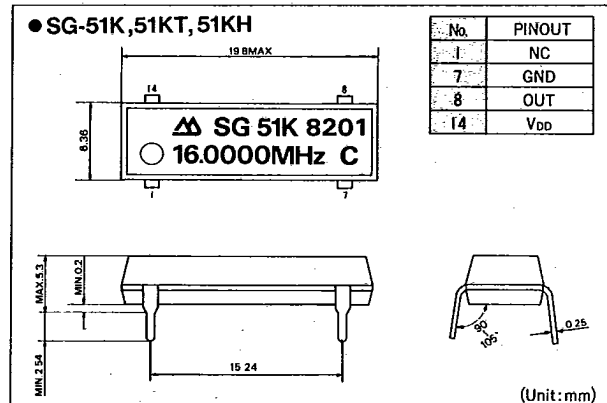
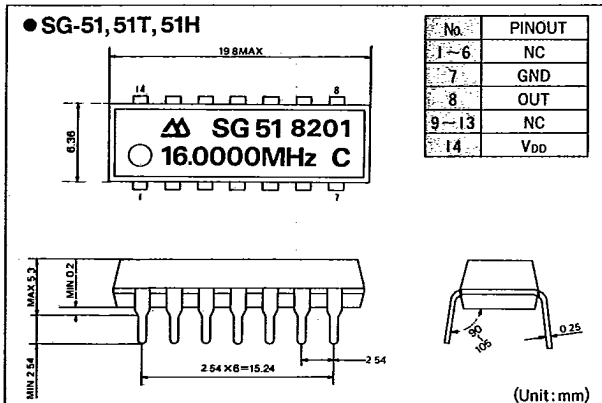
NOTES:

This test is enforced at our company. Each item is individual test.

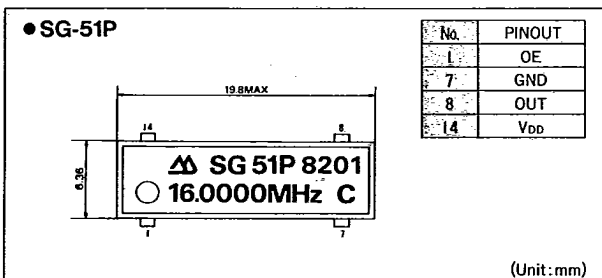
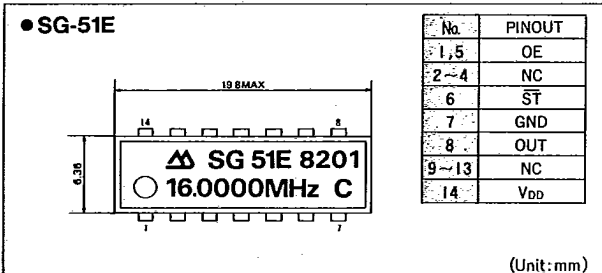
* The above-mentioned standard makes a maximum value for the frequency variation.

1. Should be satisfied with the electrical character after reliability test.
 2. Should be operated at testing atmosphere.

Dimensions



※ Indicating content give an example.



NOTES

- C-MOS IC is assembled.
Should be careful to the static electricity.
- Please put over 0.1μF capacitor in between VDD and VSS in order to keep a stability movement.
- Please put over 1ms of rise time for capacitor.
- Ultrasonic clean or insertor are available to use.
Please check the condition of the use.
- Quartz crystal is assembled.
Please don't put the excessive shock,
We'd like to recommend an ordinary temperature and humidity conditions to keep the accuracy.
- The same care should be exercised as IC.

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 3415 KASHIWA ST. TORRANCE, CA. 90505 USA.
 Phone (213)534-4500 FAX 213-539-6423

To order in America and Canada, contact:
EPSON AMERICA, INC.
 The Component Sales Department

● All specifications of this device are subject to change without notice.

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